

AMENDMENTS TO THE SPECIFICATION

Please amend page 7, paragraph number 32, as follows:

[0032] Adjacent to the transfer gate 460 and opposite to the pinned photodiode 421 is a floating diffusion region 425 for receiving charge transferred from the n-type photodiode region 426. Below the transfer gate 460 is a channel region 440 through which the current flows between the photodiode region 426 and the floating diffusion region 425. Also shown in FIG. 4 is an isolation region 428 adjacent to the pinned photodiode 421 on the side thereof opposite to the transfer gate 460.